

## **Description**

The DMP3098LSS-13 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

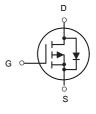


#### SOP-8

### **General Features**

 $V_{DS} = -30 V I_{D} = -5.8 A$ 

 $R_{DS(ON)} < 55 \,\text{m}\Omega$  @  $V_{GS}$ =10V



# Application

Battery protection

Load switch

Uninterruptible power supply

P-Channel MOSFET

# **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
DMP3098LSS- 3	SOP-8	HXY MOSFET	3000

# Absolute Maximum Ratings(Tc=25 °C unless otherwise noted)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	- 30	V
VGS	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Drain Current <sup>3</sup> , V <sub>GS</sub> @ 10V	-5.8	А
IDM	Pulsed Drain Current <sup>1</sup>	-20	А
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	50	°C/W



# Electrical Characteristics (T<sub>A</sub>=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	Inss	V <sub>DS</sub> =-24V,V <sub>GS</sub> =0V	-	-	-1	μΑ
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-1	-1.6	-3	V
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.1A	-	43	55	mΩ
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.2A	-	62	90	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-15V,I <sub>D</sub> =-4.5A	4	7	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss		-	520	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V,	-	130	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	70	-	PF
Switching Characteristics (Note 4)					1	
Turn-on Delay Time	td(on)		-	7	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =-15V, ID=-1A, V <sub>GS</sub> =-	-	13	-	nS
Turn-Off Delay Time	td(off)	10V,R <sub>GEN</sub> =6Ω	-	14	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	9	-	nS
Total Gate Charge	Qg		-	11	-	nC
Gate-Source Charge	Qgs	V <sub>DS</sub> =-15V,I <sub>D</sub> =-5.1A,V <sub>GS</sub> =-	-	2.2	-	nC
Gate-Drain Charge	Qgd		-	3	-	nC
Drain-Source Diode Characteristics					'	
Diode Forward Voltage (Note 3)	VsD	V <sub>GS</sub> =0V,I <sub>S</sub> =-5.1A	-	-	-1.2	V

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



# **Typical Electrical and Thermal Characteristics**

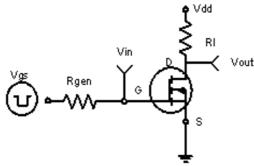


Figure 1:Switching Test Circuit

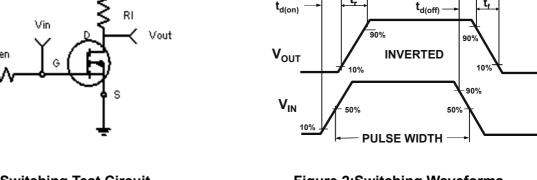
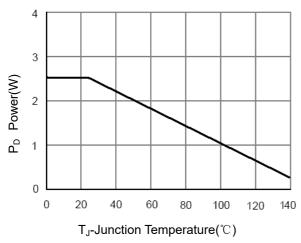
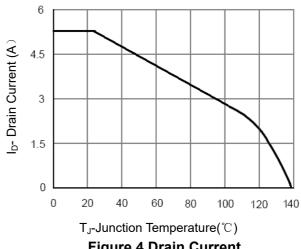


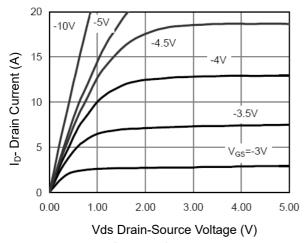
Figure 2:Switching Waveforms



**Figure 3 Power Dissipation** 



**Figure 4 Drain Current** 



**Figure 5 Output Characteristics** 

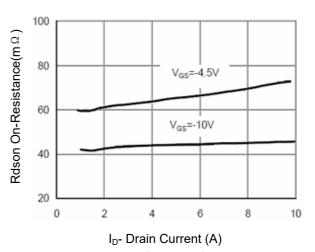
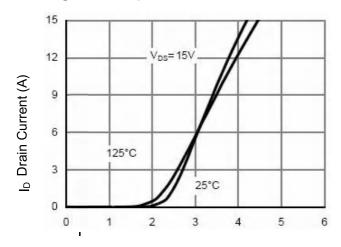


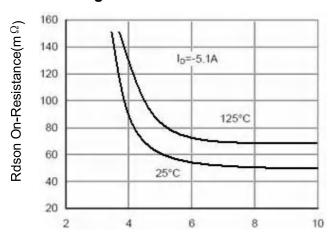
Figure 6 Drain-Source On-Resistance



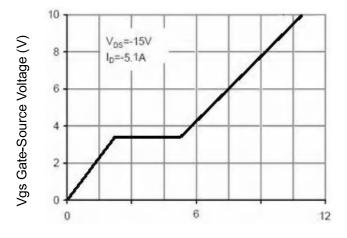
### **Figure 5 Output Characteristics**



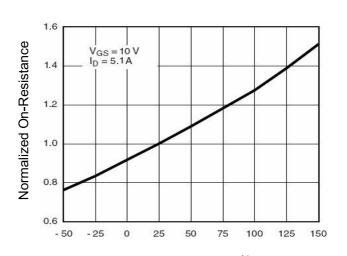
Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

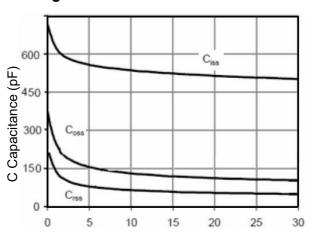


Qg Gate Charge (nC) Figure 11 Gate Charge



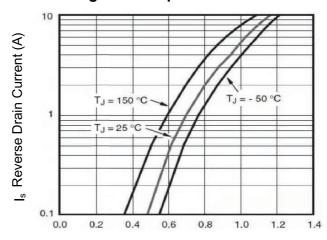
T<sub>J</sub>-Junction Temperature(°C)

Figure 8 Drain-Source On-Resistance



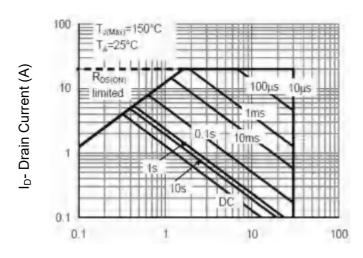
Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)
Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

**Figure 13 Safe Operation Area** 

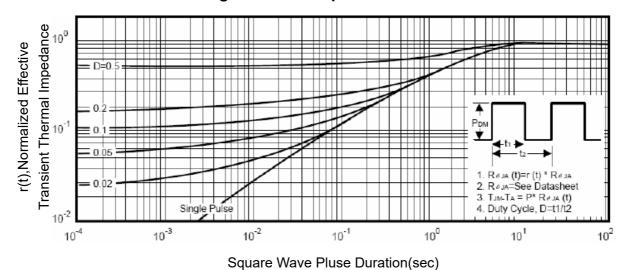
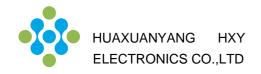
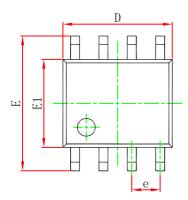
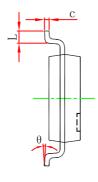


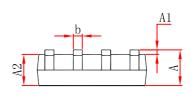
Figure 14 Normalized Maximum Transient Thermal Impedance



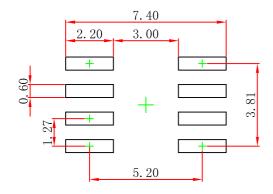
# **SOP-8 Package Outline Dimensions**







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
A	1.350	1.750	0.053	0.069	
A1	0.100	0. 250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
c	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0. 197	
e	1.270 (BSC)		0.050 (BSC)		
E	5.800	6.200	0. 228	0. 244	
E1	3.800	4.000	0.150	0. 157	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



- Note:
  1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.

#### P-Channel Enhancement Mode MOSFET

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